New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

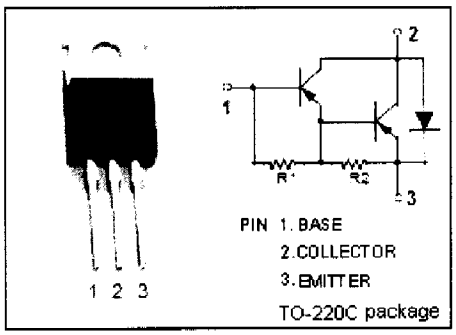
TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

Silicon PNP Darlington Power Transistor

BDW45

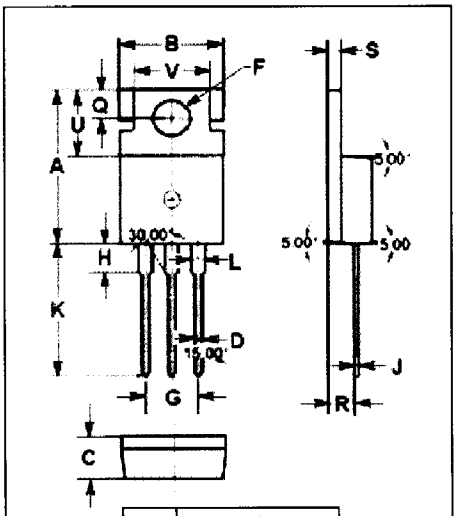
DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -60V(Min)
- High DC Current Gain
  : h_{FE}= 1000(Min) @I_C= -5A
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= -2.0V(Max.)@ I_C= -5.0A
  = -3.0V(Max.)@ I_C= -10A
- Complement to Type BDW40



APPLICATIONS

- Designed for general purpose and low speed switching applications



DIM	mm MIN	mm MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @ T_C=25℃	85	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.47	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA; I_B= 0	-60			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -5A; I_B= -10mA			-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -10A; I_B= -50mA			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -10A ; V_{CE}= -4V			-3.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-1.0	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= -30V; I_B= 0			-2.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-2.0	mA
h_{FE-1}	DC Current Gain	I_C= -5A ; V_{CE}= -4V	1000			
h_{FE-2}	DC Current Gain	I_C= -10A ; V_{CE}= -4V	250			
f_T	Current-Gain—Bandwidth Product	I_C= -3A; V_{CE}= -3V; f_{test}= 1MHz	4			MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f_{test}= 0.1MHz			300	pF